

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3	transistor and (electrode gate) and high-k and (conductive TiN HfN TaN ZrN LaN TiSi) near buffer and @ad<"20040312"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/20 18:13
L2	3	transistor and substrate and (electrode gate) and ((high near k) high-k) and (conductive TiN HfN TaN ZrN LaN TiSi) near buffer and @ad<"20040312"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/20 18:13
L3	177	transistor and substrate and (electrode gate) and ((high near k) high-k) and (conductive TiN HfN TaN ZrN LaN TiSi) with buffer and @ad<"20040312"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/20 18:14
L4	157	transistor and substrate and (electrode gate) and ((high near k) high-k) and (STI isolation) and (conductive TiN HfN TaN ZrN LaN TiSi) with buffer and @ad<"20040312"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/20 18:31
L5	129	substrate and (electrode gate) with ((high near k) high-k) with (conductive TiN HfN TaN ZrN LaN TiSi) and isolation and @ad<"20040312"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/20 18:33